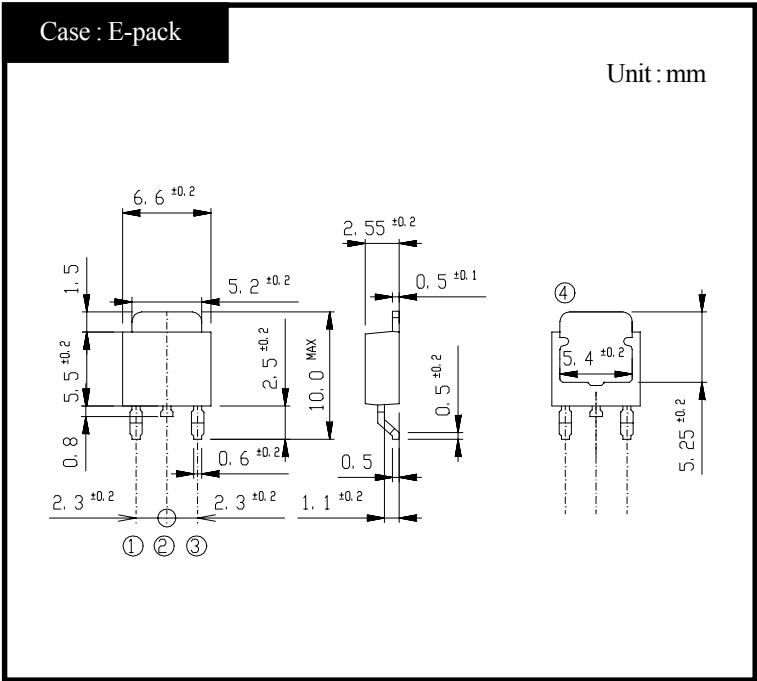


2SA1796

(TE7T4)

-7A PNP

OUTLINE DIMENSIONS



RATINGS

●Absolute Maximum Ratings

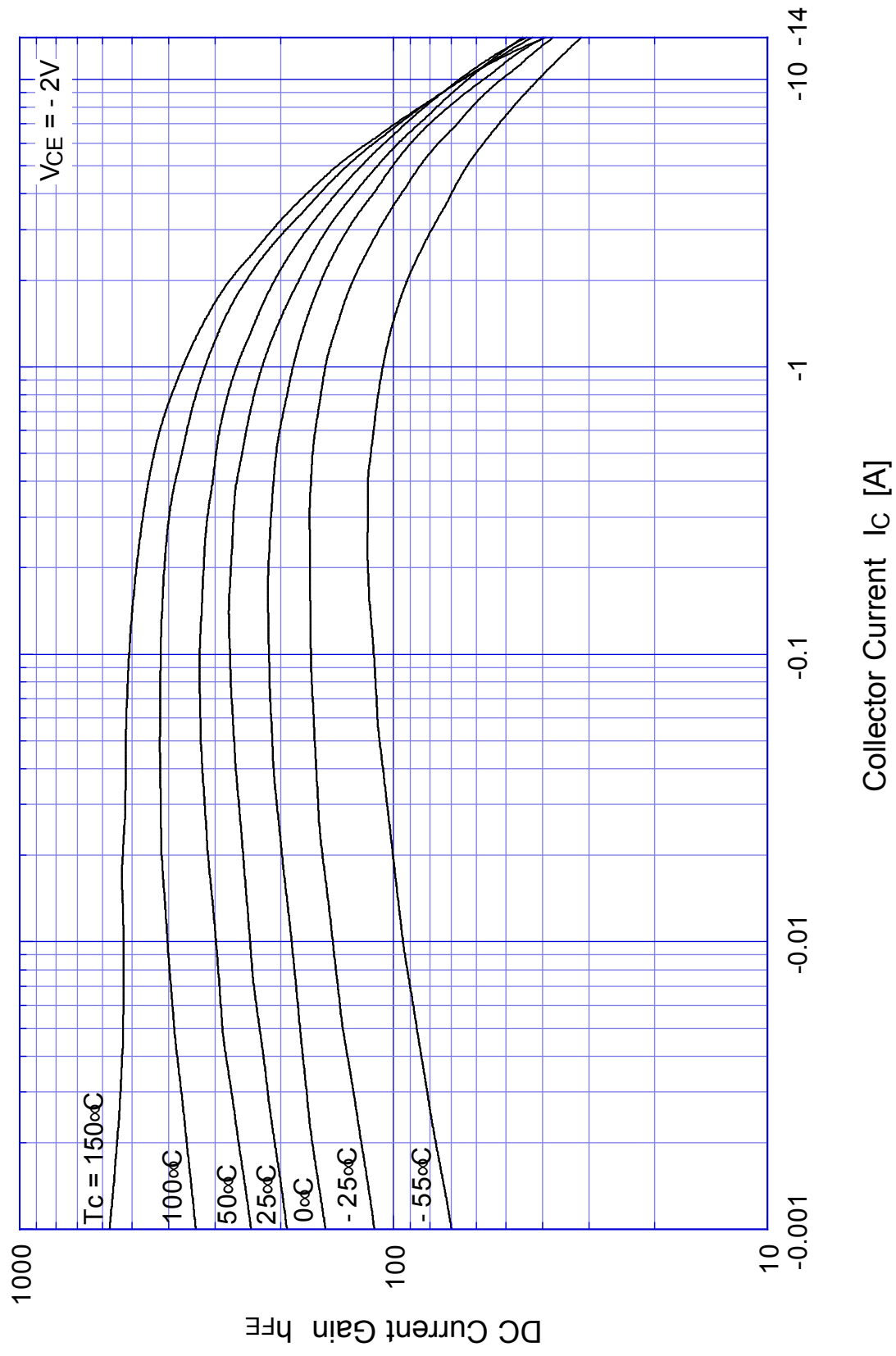
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	℃
Junction Temperature	T _j		150	℃
Collector to Base Voltage	V _{CBO}		-60	V
Collector to Emitter Voltage	V _{CEO}		-40	V
Emitter to Base Voltage	V _{EBO}		-7	V
Collector Current DC	I _C		-7	A
Collector Current Peak	I _{CP}		-14	A
Base Current DC	I _B		-1.5	A
Base Current Peak	I _{BP}		-2	A
Total Transistor Dissipation	P _T	T _c = 25℃	10	W

●Electrical Characteristics (T_c=25℃)

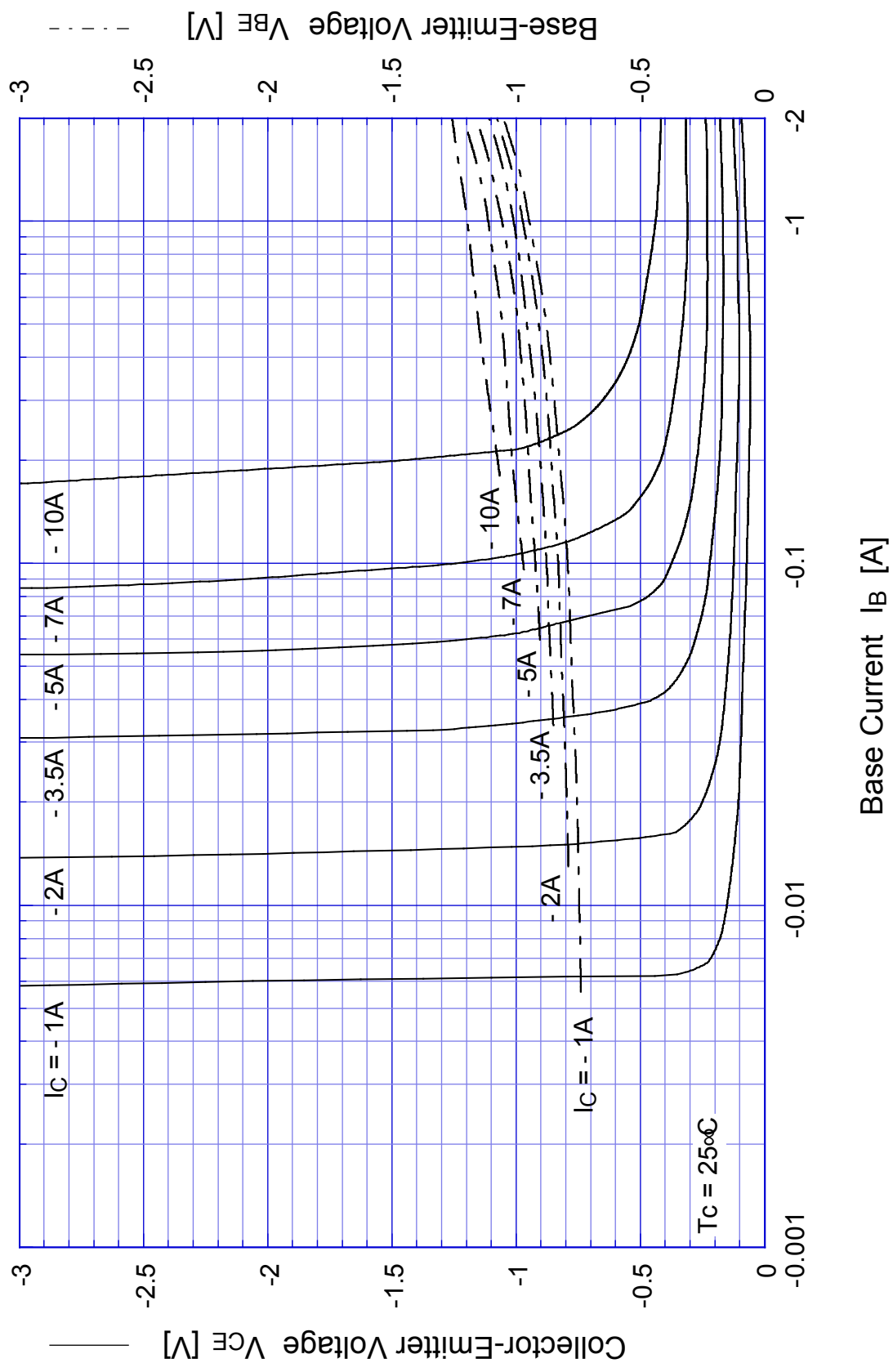
Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	V _{CEO(sus)}	I _C = -0.1A	Min -40	V
Collector Cutoff Current	I _{CBO}	At rated Voltage	Max -0.1	mA
	I _{CEO}		Max -0.1	
Emitter Cutoff Current	I _{EBO}	At rated Voltage	Max -0.1	mA
DC Current Gain	h _{FE}	V _{CE} = -2V, I _C = -3.5A	Min 70	
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C = -3.5A	Max -0.3	V
Base to Emitter Saturation Voltage	V _{BE(sat)}	I _B = -0.2A	Max -1.2	V
Thermal Resistance	θ _{jc}	Junction to case	Max 12.5	℃/W
Transition Frequency	f _T	V _{CE} = -10V, I _C = -0.7A	TYP 50	MHz
Turn on Time	ton	I _C = -3.5A I _{B1} = -0.35A, I _{B2} = -0.35A R _L = 8Ω, V _{BB2} = -4V	Max 0.3	μs
Storage Time	ts		Max 1.5	
Fall Time	tf		Max 0.5	

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$h_{FE} - I_C$

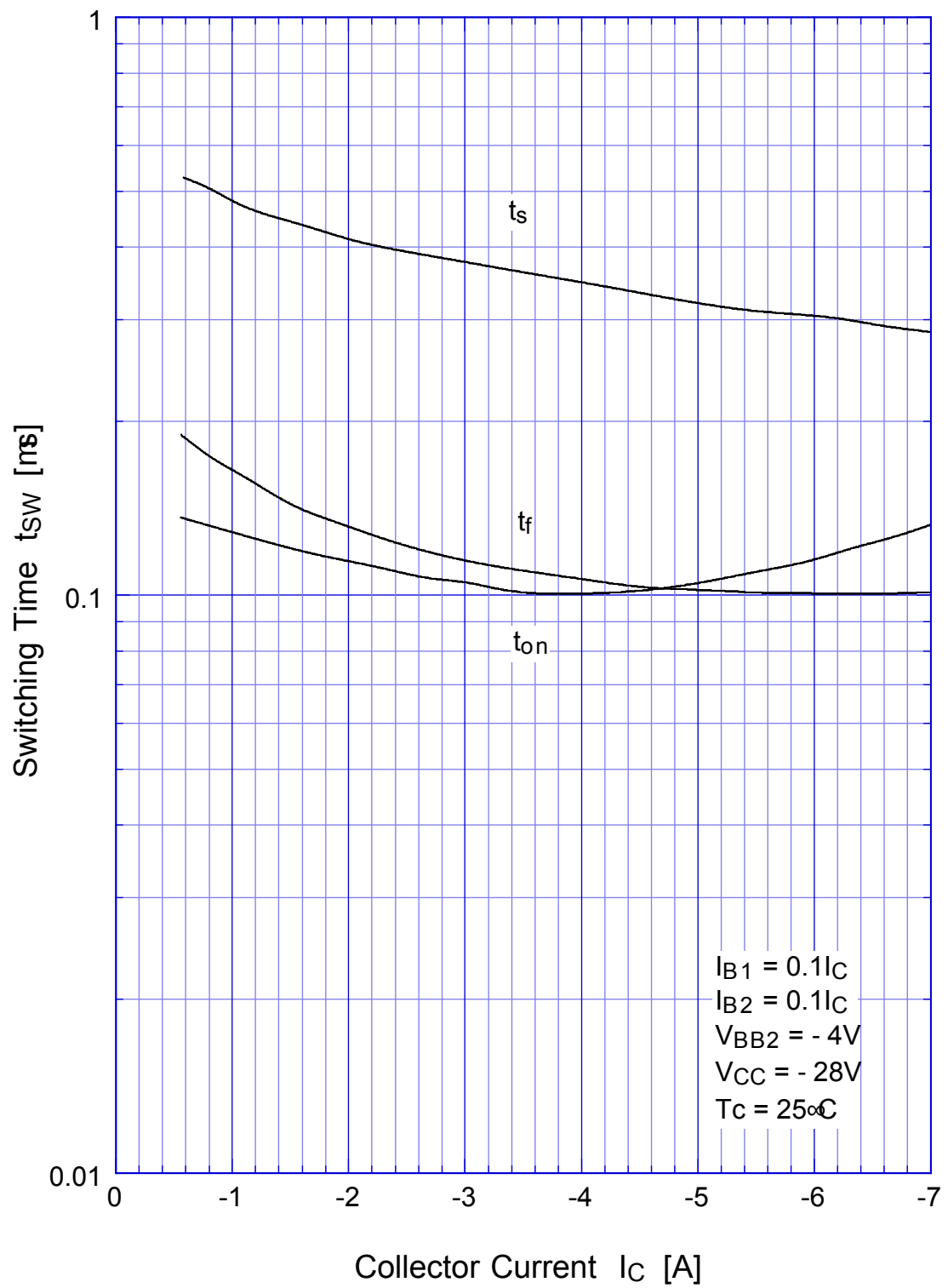


2SA1796 Saturation Voltage



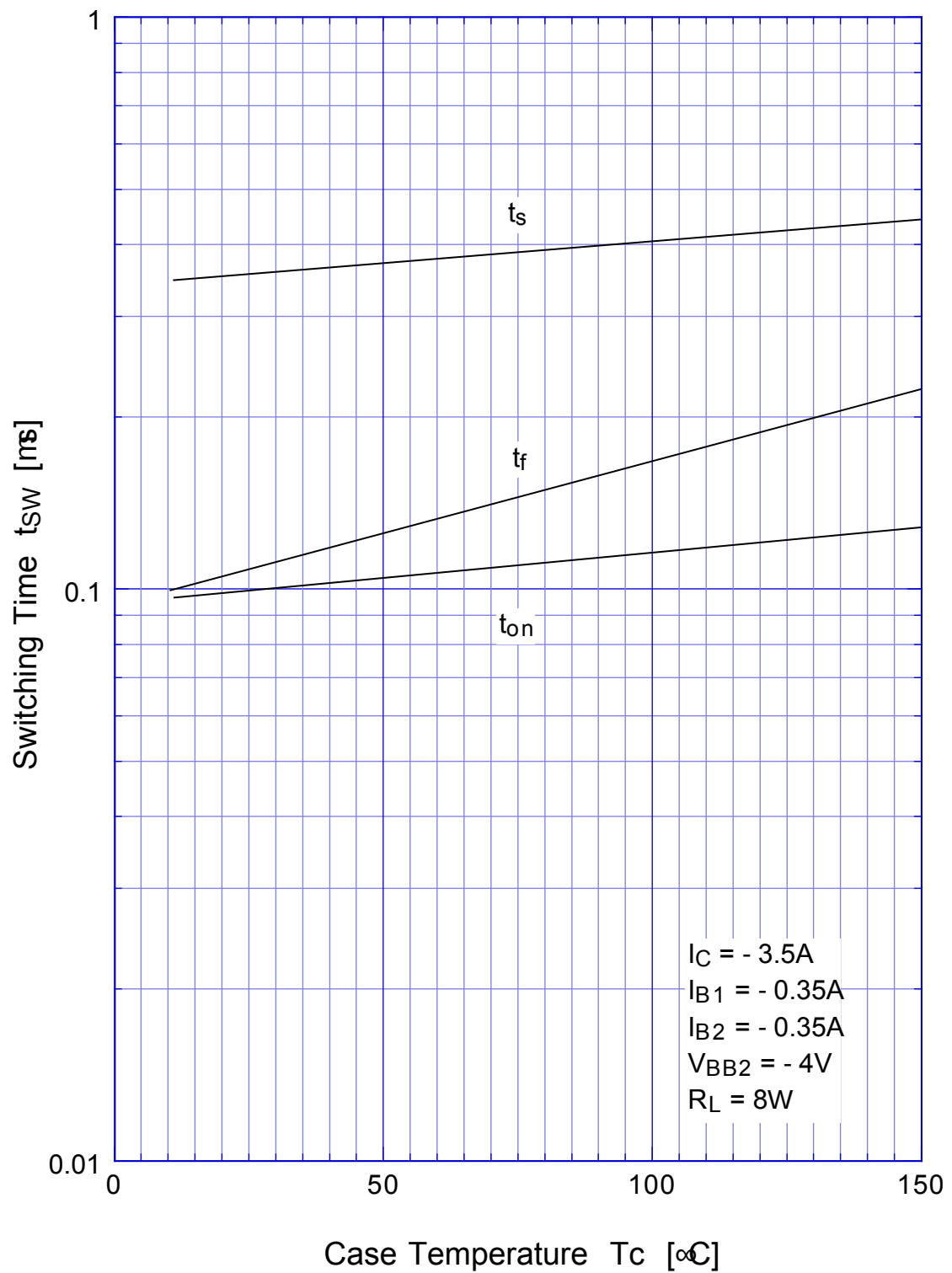
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Switching Time - I_C

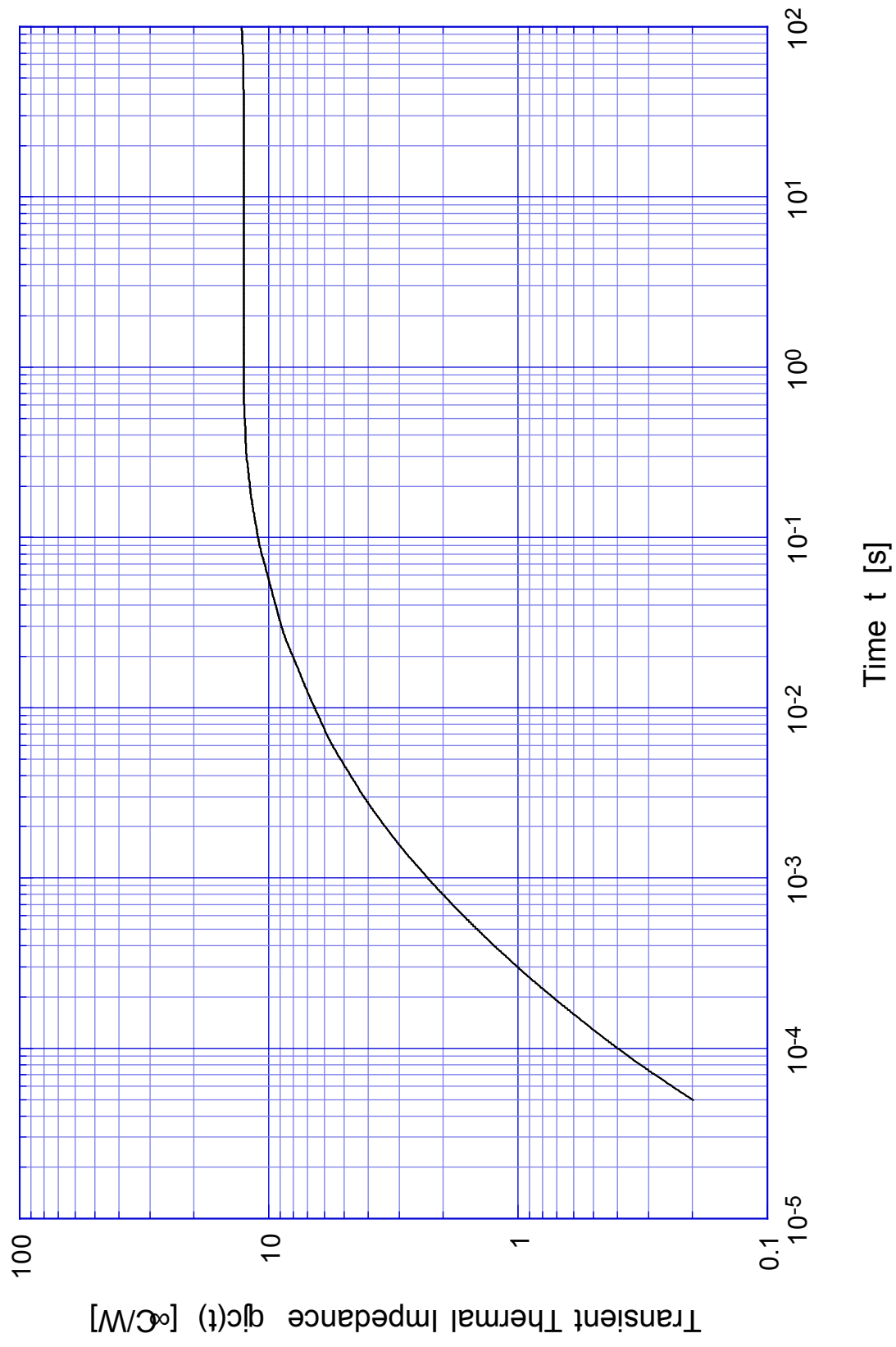


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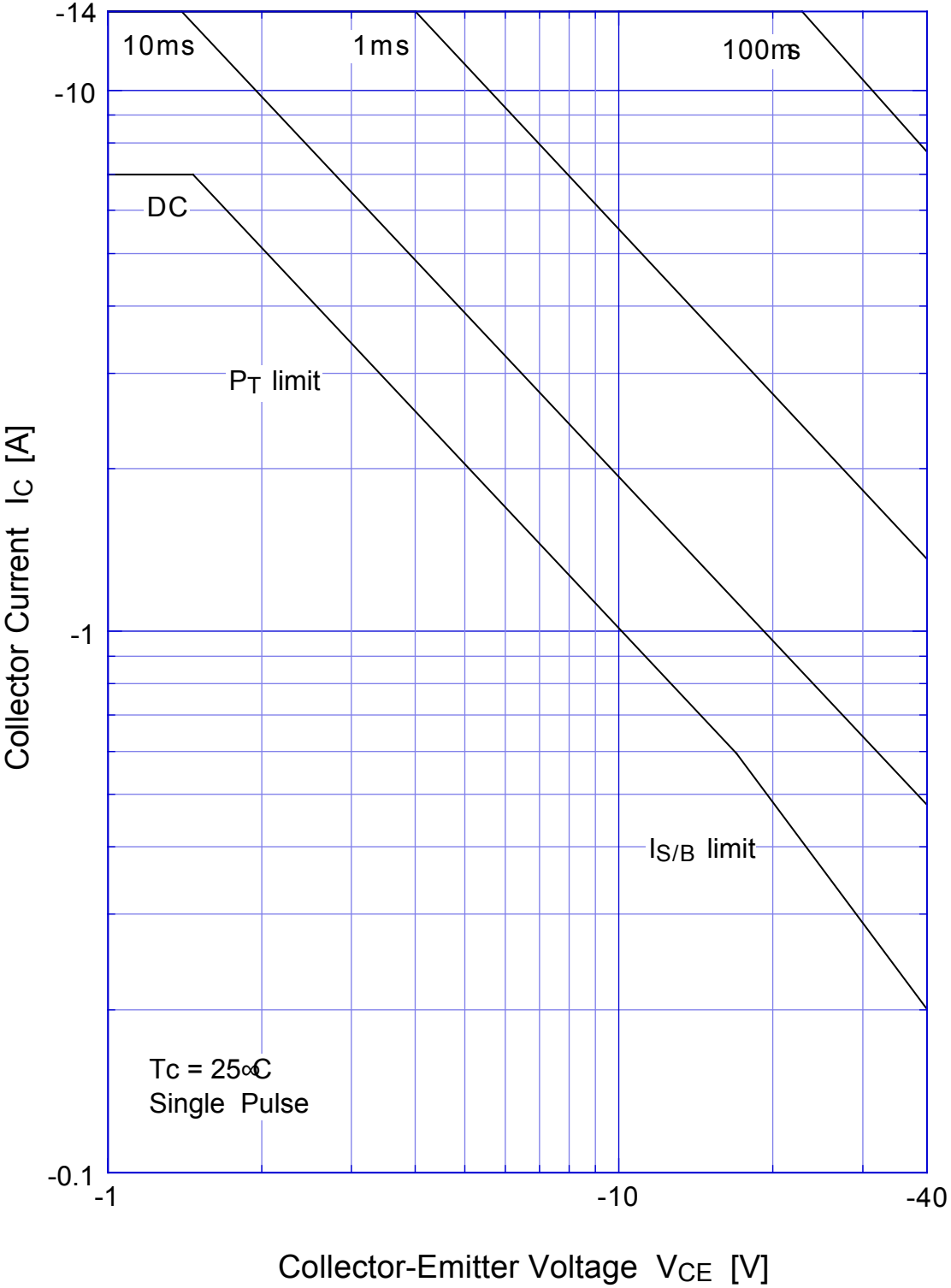
Switching Time - T_c



2SA1796 Transient Thermal Impedance

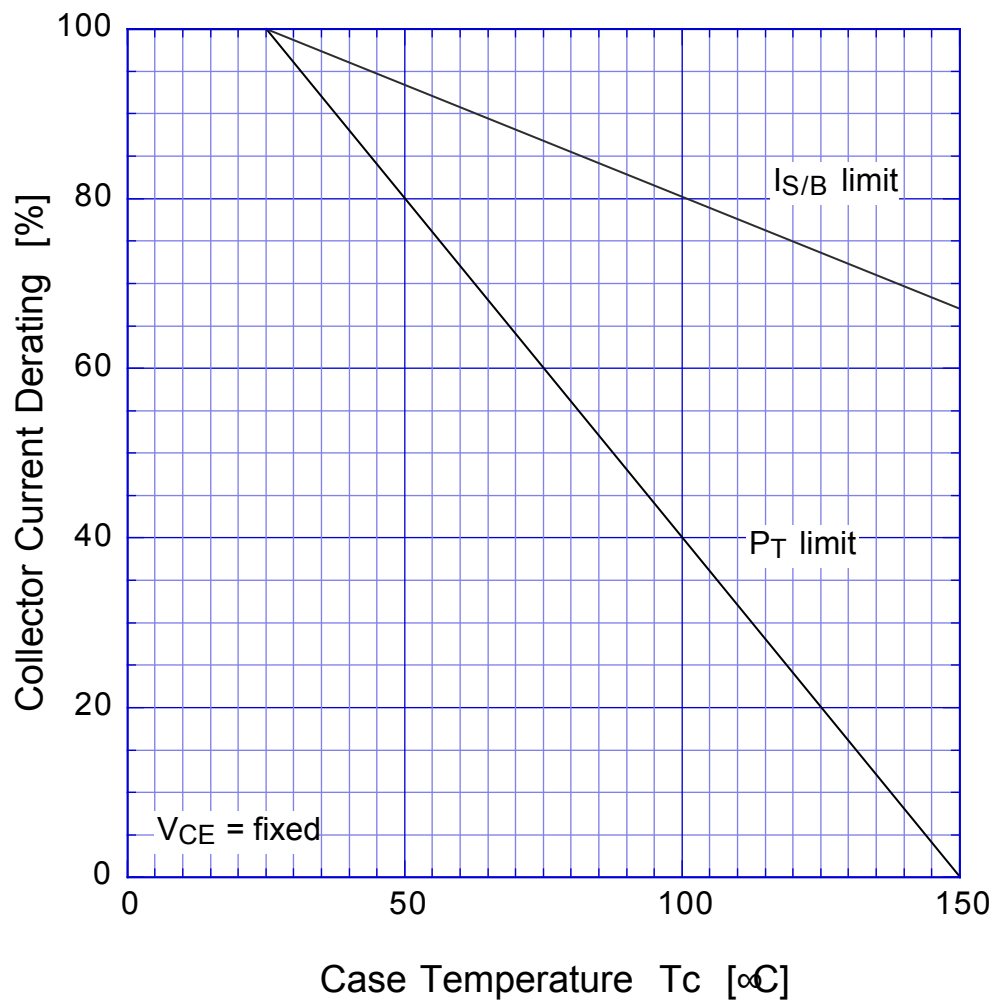


2SA1796 Forward Bias SOA



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Collector Current Derating



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Reverse Bias SOA

